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COJ

Patent No. 7,084,455

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Date 9/14/07

Signature: Joanne Ryan
Joanne Ryan

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

APPLICANT(S) : Richard A. Blanchard

PATENT NO. : 7,084,455 B2

ISSUED : August 1, 2006

TITLE : POWER SEMICONDUCTOR DEVICE HAVING A VOLTAGE SUSTAINING REGION THAT INCLUDES TERRACED TRENCH WITH CONTINUOUS DOPED COLUMNS FORMED IN AN EPITAXIAL LAYER

DOCKET : GS 159 D1

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Certificate
SEP 20 2007
of Correction

REQUEST FOR CERTIFICATE OF CORRECTION

Applicant's attorney, on behalf of the Assignee of record, hereby requests the issuance of a Certificate of Correction for the following Applicant errors pursuant to 35 USC §255 and for the following Patent Office errors pursuant to 35 USC §254:

SEP 20 2007

Correction is requested for the following Patent Office errors:

Col. 3, line 12, begin new paragraph and add

--Accordingly, it would be desirable to provide a method of fabricating the MOSFET structure shown in FIG. 3 that requires a minimum number of epitaxial deposition steps so that it can be produced less expensively while also allowing sufficient control of process parameters so that a high degree of charge compensation can be achieved in adjacent columns of opposite doping type in the drift region of the device.--

Col. 5, line 17, after "trench", change "5201" to --520₁--.

Col. 5, line 25, after "layer", change "524," to --524₁--.

Correction is requested for the following Applicant errors:

Abstract, line 18, after "the", change "another" to --other--.

Col. 3, line 33, after "the", change "another" to --other--.

Col. 5, line 9, after "layer", change "502" to --501--.

Col. 6, line 31, after "encompasses", delete --a--.

Col. 6, line 39, after first word "The", change "polysilcon" to --polysilicon--.

Patent No. 7,084,455

The PTO is hereby authorized to charge the undersigned attorney's PTO deposit account #50-1047 accordingly.

A PTO-1050 is enclosed; a Certificate of Correction is respectfully requested.

Respectfully submitted:



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SEP 20 2007

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO : 7,084,455 B2

DATED : August 1, 2006

INVENTOR(S): Richard A. Blanchard

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Abstract, line 18, after "the", change "another" to --other--.

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PATENT NO.

No. of additional copies 1

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete the form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1350.

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